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TITLE : COMPOSITION FOR FORMING FILM, FORMATION OF FILM AND LOW- DENSITY FILM

ABSTRACT : PROBLEM TO BE SOLVED: To obtain a composition for forming a film having excellent dielectric constant characteristics, mechanical strength, etc.

SOLUTION: This composition for forming a film comprises (A) a silane compound which is a hydrolyzate and a condensate or either of the hydrolyzate and the condensate of at least one compound selected from the group consisting of a compound of the formula, $R_1aSi(OR_2)_4-a$ (R_1 is a hydrogen atom, a fluorine atom or a monofunctional organic group; R_2 is a monofunctional organic group; and a is an integer of 0-2) and a compound of the formula, $R_3b(R_4O)_3-bSi-(R_7)_d-Si(OR_5)_3-cR_6c$ (R_3 , R_4 , R_5 and R_6 are each the same or different and a monofunctional organic group; b and c are each the same or different and an integer of 0-2; R_7 is an oxygen atom or a group of $-(CH_2)_n$; n is 1-6; and d is 0 or 1), (B) a latent basic catalyst and (C) a compound which is compatible or dispersible in the component A and has 250-450°C decomposition temperature.

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